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PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of: Eung-Youl KANG

Serial No.: 09/746,459

Group Art Unit: 2814

Filed: December 26, 2000

Examiner: Farahani, Dana

For: FERROELECTRIC RANDOM ACCESS MEMORY DEVICE

\* \* \* \* \*

AMENDMENT

Honorable Commissioner for Patents  
Washington, D.C. 20231

March 12, 2003

Sir:

Responsive to the Office Action mailed November 29, 2002  
(Paper No. 5), kindly enter the following amendments and remarks.

IN THE CLAIMS:

Please amend claims 1 and 5 to read as follows:

1. (Twice Amended) A ferroelectric memory cell for use in a ferroelectric random access memory (FeRAM) device, the ferroelectric memory cell comprising:

a first active area incorporating therein a gate of a depletion mode transistor and operating as a bit line;

a second active area adjacent to the first active area and incorporating therein a gate of an enhancement mode transistor;

a word line coupled to the gate of the depletion mode transistor and the gate of the enhancement mode transistor; and

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